100 GHz PHOTODETECTOR MODULE





AT A GLANCE

high-speed photodetector module for > 1 T/bs PAM datacom, telecom and microwave photonics applications

Features

- up to 100 GHz 3 dB-bandwidth
- detection of 128 GBaud amplitude modulated signals
- operation in O-band and C+L-band
- integrated bias network
- low bias operation
- 1 mm RF connector

Applications

- datacommunication
- telecommunication
- test- & measurement systems
- microwave photonics

Technical Background

High-speed photodetector modules are of interest for the development of nextgeneration optical communication links in datacom and telecom. Since these R&D links are always a step ahead in terms of symbol rates, photodetector modules with a RF bandwidth beyond state-of-the-art are needed at the receiver side. Furthermore, the highspeed performance of the photodetector modules makes them applicable to microwave photonics.

The photodetector chips inside the modules are based on mature InP technology and are fabricated at the wafer process line of HHI, offering Telcordia and space-qualified processes. The chips are packaged at HHI facilities.









107 GB/s PRBS sequence



2.4 ps FWHM input pulse

Technical Specifications

• 3 dB-bandwidth: up to 100 GHz

- C+L-band option wavelength: 1480 nm - 1620 nm responsivity: 0.5 A/W @ 1550 nm
- O-band & C+L-band option wavelength: 1270 nm - 1620 nm responsivity: 0.45 A/W @ 1550 nm 0.5 A/W @ 1310 nm
- PDL: < 0.5 dB
- optical input power: up to +15 dBm
- dark current: < 100 nA @ 3 V
- bias voltage: +2 V
- 1 mm female RF connector
- RF output matched to 50Ω
- optical input: FC/APC SMF fibre

Dr.-Ing. Patrick Runge Photonic Components

Phone +49 30 31002-498 patrick.runge@hhi.fraunhofer.de

Fraunhofer Heinrich Hertz Institute Einsteinufer 37, 10587 Berlin Germany

www.hhi.fraunhofer.de/pc